



	°C					
	°C					
	°C					
	°C					
	°C					
	°C					
	°C					



FIG.1: Power dissipation vs. on-state current
(per thyristor or diode)

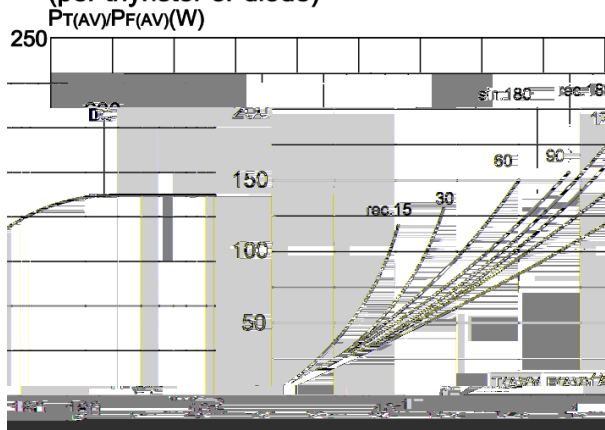


FIG.2: Maximum transient thermal impedance
junction to case(per thyristor or diode)

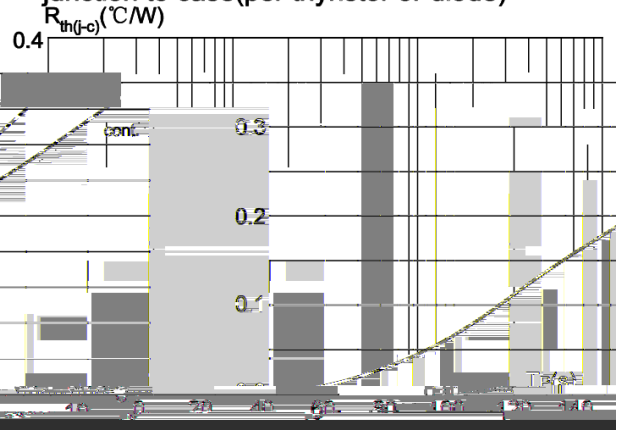


FIG.3: Forward characteristics
(per thyristor or diode)

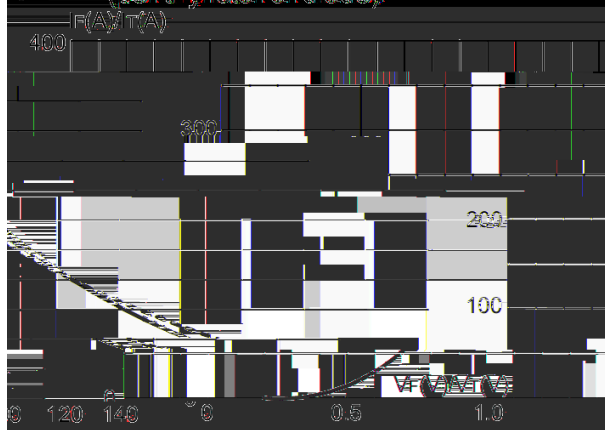


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature
 $I_{GT}(T)/I_{GT}(T_{25^{\circ}C})$, $I_H(T)/I_H(T_{25^{\circ}C})$, $I_L(T)/I_L(T_{25^{\circ}C})$

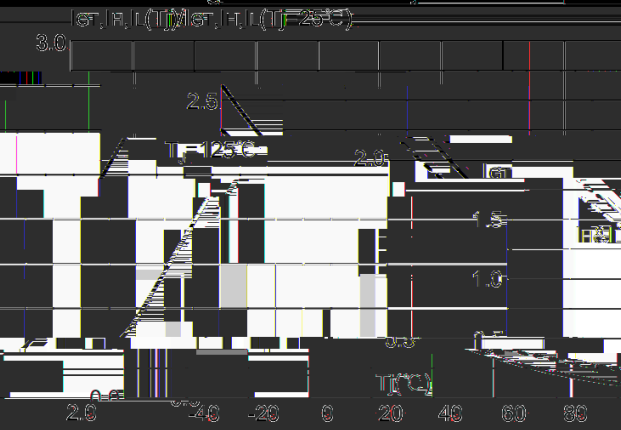


FIG.5: Gate trigger characteristics
 V_{GT}

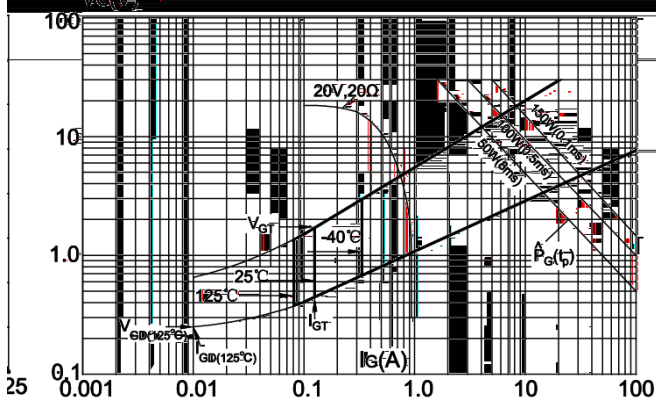


FIG.6: Forward current vs. case temperature
 $I_{FAW}(A)$ (per thyristor or diode)

